

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	0	method near5 voi adj1 free	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
2	BRS	L2	9	method near5 void adj1 free adj layer	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
3	BRS	L3	179619 8	flip adj1 chip neae1 assembl\$2	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
4	BRS	L4	286	method near5 void adj1 free	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
5	BRS	L5	7570	encapsulant	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB

	Type	L #	Hits	Search Text	DBs
6	BRS	L6	225	inject\$3 near2 encapsulant	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
7	BRS	L7	77	microelectronic adj1 equipment	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
8	BRS	L9	2	5 and 8	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
9	BRS	L11	0	7 and 10	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
10	BRS	L10	2	6 and 9	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB

	Type	L #	Hits	Search Text	DBs
11	BRS	L12	68	3 and 4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
12	BRS	L14	2	6 and 13	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
13	BRS	L15	0	7 and 14	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
14	BRS	L8	6	2 and 3	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
15	BRS	L13	5	5 and 12	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB

	Type	L #	Hits	Search Text	DBs
16	BRS	L17	47	pressure and energy near5 encapsulant	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
17	BRS	L18	0	16 and 17	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
18	BRS	L19	0	4 and 16	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
19	BRS	L20	2	4 and 17	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
20	BRS	L21	62965	(hole\$1 or gap) near5 substrate	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB

	Type	L #	Hits	Search Text	DBs
21	BRS	L22	36	4 and 21	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
22	BRS	L24	2	6 and 23	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
23	BRS	L23	4	5 and 22	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB
24	BRS	L16	20	gap near10 (chip and substrate)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TDB

	U	1	Document ID	Title	Current OR
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20010019852 A1	SEMICONDUCTOR DEVICE, METHOD OF MAKING THE SAME, CIRCUIT BOARD, FLEXIBLE  SUBSTRATE, AND METHOD OF MAKING SUBSTRATE	
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6265236 B1	Method for the manufacture of a light emitting diode	438/22
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6232145 B1	Method and apparatus for filling a gap between spaced layers of a  semiconductor	438/106
4	<input type="checkbox"/>	<input type="checkbox"/>	US 6214635 B1	Method and apparatus for underfill of bumped or raised die	438/51
5	<input type="checkbox"/>	<input type="checkbox"/>	US 6066509 A	Method and apparatus for underfill of bumped or raised die	438/51
6	<input type="checkbox"/>	<input type="checkbox"/>	US 6048656 A	Void-free underfill of surface mounted chips	430/118
7	<input type="checkbox"/>	<input type="checkbox"/>	US 6037043 A	UV-hardenable and thermally hardenable epoxy resins for underfilling  electrical and electronic components	428/209
8	<input type="checkbox"/>	<input type="checkbox"/>	US 5973404 A	Underfill of bumped or raised die using a barrier adjacent to the  sidewall of semiconductor device	257/778
9	<input type="checkbox"/>	<input type="checkbox"/>	US 5898192 A	Light emitting diode with improved luminous efficiency having a contact  structure disposed on a frosted outer surface	257/98

	U	1	Document ID	Title	Current OR
10	<input type="checkbox"/>	<input type="checkbox"/>	US 5886369 A	Epitaxial wafer for GaP pure green light-emitting diode and GaP pure green light-emitting diode	257/86
11	<input type="checkbox"/>	<input type="checkbox"/>	US 5866442 A	Method and apparatus for filling a gap between spaced layers of a semiconductor	438/108
12	<input type="checkbox"/>	<input type="checkbox"/>	US 5814882 A	Seal structure for tape carrier package	257/704
13	<input type="checkbox"/>	<input type="checkbox"/>	US 5766982 A	Method and apparatus for underfill of bumped or raised die	438/51
14	<input type="checkbox"/>	<input type="checkbox"/>	US 5373627 A	Method of forming multi-chip module with high density interconnections	29/841
15	<input type="checkbox"/>	<input type="checkbox"/>	US 5300792 A	Gap red light emitting diode	257/101
16	<input type="checkbox"/>	<input type="checkbox"/>	US 5005638 A	Thermal conduction module with barrel shaped piston for improved heat transfer	165/80.4
17	<input type="checkbox"/>	<input type="checkbox"/>	US 4896109 A	Photoconductive circuit element reflectometer	324/765
18	<input type="checkbox"/>	<input type="checkbox"/>	US 4870295 A	Photoconductive circuit element pulse generator	250/208.2
19	<input type="checkbox"/>	<input type="checkbox"/>	US 4825284 A	Semiconductor resin package structure	257/717
20	<input type="checkbox"/>	<input type="checkbox"/>	JP 07176013 A	Magnetic head manufacturing method for VTR - involving formation of symmetrical pair of head chips in gaps on head substrate	

	U	1	Document ID	Title	Current OR
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6107123 A	Methods for providing void-free layers for semiconductor assemblies	438/125
2	<input type="checkbox"/>	<input type="checkbox"/>	US 5834339 A	Methods for providing void-free layers for semiconductor assemblies	438/125
3	<input type="checkbox"/>	<input type="checkbox"/>	US 5710071 A	Process for underfilling a flip-chip semiconductor device	438/108
4	<input type="checkbox"/>	<input type="checkbox"/>	US 5834339 A	Methods for providing void-free layers for semiconductor assemblies	